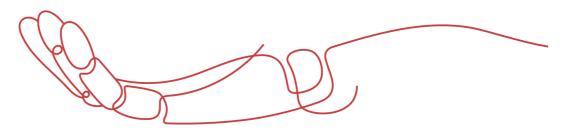


PRODUCT DATA SHEET



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Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

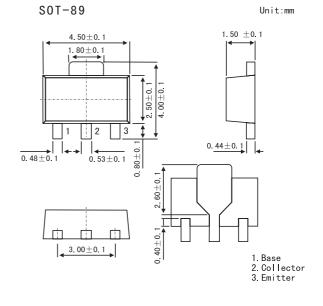


FCX690BTA

NPN Silicon Power Switching Transistor

Features

- 2W power dissipation.
- 6A peak pulse current.
- Gain of 400 @lc=1Amp.
- Very low saturation voltage.



Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|-----------------------------------------|---------|-------------|------|
| Collector-base voltage | Vсво | 45 | V |
| Collector-emitter voltage | Vceo | 45 | V |
| Emitter-base voltage | Vebo | 5 | V |
| Continuous collector current | Ісм | 6 | А |
| Peak pulse current | lc | 2 | А |
| Power dissipation | Ptot | 1 | W |
| Operating and storage temperature range | Tj,Tstg | -55 to +150 | °C |





Electrical Characteristics Ta = 25 $^{\circ}$ C

| Parameter | Symbol | Testconditons | Min | Тур | Max | Unit |
|----------------------------------------|----------|-------------------------------------------------|-------------------|------|-----------|------|
| Collector-base breakdown voltage | V(BR)CBO | Ic=100µA | 45 | | | V |
| Collector-emitter breakdown voltage * | V(BR)CEO | Ic=10mA | 45 | | | V |
| Emitter-base breakdown voltage | V(BR)EBO | Iε=100μA | 5 | | | V |
| Collector Cut-Off Current | Ісво | Vcb=9V | | | 0.1 | μA |
| Emitter Cut-Off Current | Іево | VEB=4V | | | 0.1 | μA |
| Collector-emitter saturation voltage * | VCE(sat) | Ic=0.1A, Iв=0.5mA Ic=1A, Iв=5mA | | | 80 300 | mV |
| Base-emitter saturation voltage * | VBE(sat) | Ic=1А, Iв=10mА | | | 1.1 | V |
| Base-emitter ON voltage * | VBE(on) | IC=1A, VCE=2V | | | 1.0 | V |
| Static Forward Current Transfer Ratio* | hfe | Ic=100mA,Vce=2V Ic=1A,Vce=2V Ic=2A,Vce=2V | 500 400 150 | | | |
| Transitional frequency | fτ | Ic=50mA, Vce=5V, f=50MHz | 150 | | | MHz |
| Input capacitance | Cibo | Veb=0.5V, f=1MHz | | 200 | | pF |
| Output capacitance | Cobo | Vсв=10V, f=1MHz | | 16 | | pF |
| Turn-on time | t(on) | Ic=500mA, Vcc=10V | | 33 | | ns |
| Turn-off time | t(off) | Ів1=Ів2=50mA | | 1300 | | ns |

* Pulse test: tp = 300 μ s; d \leq 0.02.





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